Performance analysis of High Speed ADC using SR F/F

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Abstract: This paper present a new design of comparator for flash ADC. The flash ADC is the fastest Application ADC that requires the high speed comparator. The new design consist of sense amplifier and SR Latch ,the combining configuration of design have the considerable stable output which helps in high speed and resolution. The use of SR symmetric latch makes stable output as compared to the conventional SR latch moreover the design has high resolution. This paper has been done in 180 nm and 90nm gpdk in CADENCE VIRTUOSO. For low power application. There are many issues in the design of the comparator, we will discuss those design issues in this paper.

I. Introduction

The design of comparator is the most critical part in the flash ADC, since the speed and the resolution is determined by the comparator. The dual tail current sense amplifier based comparator can run faster with lower supply voltage than the normal one, and the kick back effect is also better than the normal one. The symmetric S-R latch provides shorter delay time and stable time than the normal S-R latch. Combing the sense amplifier based comparator and the symmetric S-R latch, the whole block can run faster and the output signal is more stable than the normal structure. This design of comparator is for 2GSample/sec flash ADC. Based on IEEE 802.15.3a WPAN UWB applications, the signals using multi-band orthogonal frequency division multiplexing (MB-OFDM) occupy a bandwidth of 528MHz for every band. It requires the conversion rate at least higher than 1.06GSample/sec.

1.1. The Analysis Of The Traditional Sense Amplifier Based Comparator And Sr Latch:

In the analysis of any comparator there are 2 stages in which operation is divided, one is reset phase and other is regeneration phase. In this sense amplifier based comparator sense amplifier connects positive feedback with the resistive input as shown in fig.1.Now during reset phase when clock is low, the nodes of inverters (M1-M4) are charged to Vdd, through transistor M7 and M8. Again on regeneration phase when clock is high Nmos transistor M9 is turned on which is a part of differential pair M5 and M6. Current flowing through this pair controls the latch circuit and small changes between differential pair cause large output change. And this differential pair discharge the node Ni, and later difference of the input voltage will built charge it. When Ni come to Vth voltage then inverter M1,M3 turns on and this will start the positive feedback. After Ni comes to 2Vth below Vdd transistor M2,M4 are turn on. Now with the help of strong positive feedback small input converted to full differential output.

For the generation of output there is very short period of time in sense amplifier when its gain is good.so switch M11, M12 is added to increase the integration time. In the conventional sense amplifier, it is better to add a reset switch (M11, M12) connecting the Vdd and the Di so as to increase the integration time. In the sense amplifier there is only a very short time in which the differential pair actually have the gain. Actually the differential pair comes to triode region during Ni drop to Vth. This reset transistor also increase the active time of differential pair and decrease the offset effect in coming signals.

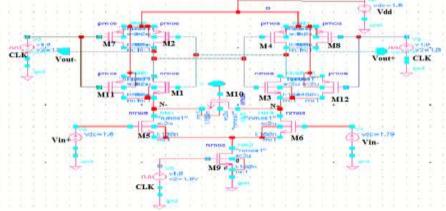


Fig.1: Conventional Sense Amplifier Based Comparator

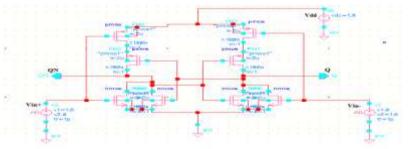


Fig.2: Conventional S-R Latch

M10 is added to prevent output signal to becomes floating. From the above analysis it is found out that there is a trade of between integration time and regeneration time.

To get stable output S-R latch is inserted after the comparator.S-R latch is made up of two NOR gates in which while R is high then its output Q become low and /Q becomes high and vise-versa. And when S is high Q will be high and /Q is low. Hence one of the output is always delayed with the other and both output Q and /Q depends on each other, shown in fig.3.

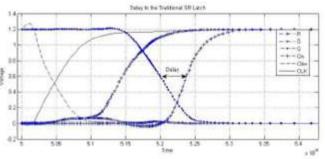


Fig.3: Delay between Q and /Q of SR Latch

1.2. Double Tail Current Sense Amplifier Based Comparator With Symmetric Sr Latch:

1.2.1. Double Tail Current Sense Amplifier Based Comparator[1]:-

The circuit of double tail current sense amplifier is based on division of tail current. All the limitation amplifier of sense is trade off in tail current. The tail current of transistor M9 in fig 1 is divided in to M9 and M10 for performance enhancement.

Operation :

During the reset phase (CLK = 0V)

Transistor M7 and M8 pre-charge the Di nodes to Vdd, which in turn causes M11 and M12 to discharge the output nodes to ground, and because of the discharge function of M11 and M12, there is no need to add an additional reset switch between the output nodes.

After the reset phase:

The tail current transistor M9 and M10 turn on when CLK = V dd. At the common mode voltage at the nodes Di is dropped at the rate of the I M9/C Di, and the difference input voltage caused difference nodes voltage is build up at the nodes Di by integration onto the capacitance at the Di nodes. The intermediate stage formed by M11 and M12 passes VDi to the cross-coupled inverters. The cross coupled inverters starts to regenerate the voltage difference as soon as the common-mode voltage at the Di is not strong enough to clamp the outputs to ground. Compared with the traditional sense amplifier, the intermediate stage add one more stage isolation, so as provides additional shielding between input and output. Because the effective amplification factor equals the integrator gain, GM5,M6/CDi, times the integration time, proportional to CDi/Itail. It is better to use the small transistor as the tail current and the large input differential pair.

The delay of the improved sense amplifier based comparator is consists of two parts. First is the integration time or sampling interval of the input differential pair. The second part of the delay is from the latch regeneration time. The first part of the delay have the relation to the actually gain of the input differential pair and to the offset of the whole comparator, the second one has the relation to the speed of the latch, and both of them is controlled by the tail current. Because the integration time and the latch regeneration time is controlled by the different tail current, the totally delay can be optimized so as to have the maxim performance. Maxim the first delay, the integration time, and minim the second delay. The most important contribution to the

offset in the improved sense amplifier based comparator is come from the input differential pair, M5 and M6. In order to decrease the offset effect from the M5 and M6, we want to use the bigger sized transistor. The input offset of the comparator and the preamplifier is 7.3mV.

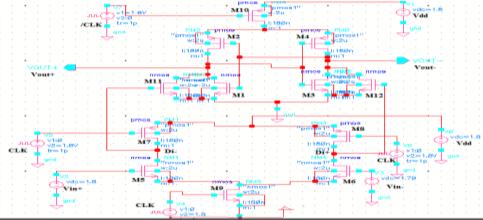


Fig.4: Double tail Current sense Amplifier Based Comparator

1.2.2. Symmetric S-R Latch:-

The main problem comes from the non-symmetry of the SR latch structure . In order to overcome the non-symmetric problem, we can modify the structure. First do the simplicity of the expression, Q represent the present, Q+ represents the next state. From the Karnaugh map for $Q_{+} = f(S,R,Q)$, we can separate the logic description of the S-R latch.

 $\mathbf{Q} + = \mathbf{\bar{S}} + \mathbf{R} \cdot \mathbf{Q} \ (1)$

 $\mathbf{Q} + = \mathbf{R} + \mathbf{S} \cdot \mathbf{Q} \ (2)$

The Equ.{1,2} is applied to the NMOS and PMOS network. And the whole Karnaugh map is divided into '0' and '1' which is achieved separately by NMOS and PMOS. And, finally the result is achieved by combing Equ.1 Equ.2 only. The circuit is shown in the Fig.5. Because of the symmetric design flow of the S-R latch, we can use the small keeper transistor since only one transistor is active in the each branch when changing the state. And, because we divided the whole Karnaugh map into two part, that is 1 and 0 or true and complementary trees, the delay of the S-R latch is the same in this structure. Further, we can divided the whole structure into the keeper transistor ({M8,M9,M11,M12},{M2,M3,M5,M6}) and the driver transistor ({M1,M7,M4,M10}). In each transition, the keeper transistor should change the state fast so the size of them should be small, and the driving transistors should be bigger compare with the keeper transistor so as to drive the load. The divide of the S-R latch make the design and optimization straightforward.

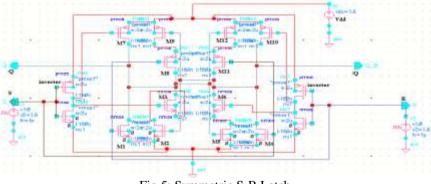


Fig.5: Symmetric S-R Latch

1.2.3. Double Tail Comparator with the Symmetric S-R Latch[2][3]:-

Combing the Sense Amplifier based Comparator and the S-R latch forms the Sense Amplifier Flip Flop (SAFF). In the Flip Flop, the comparator used as the pulse generator and the S-R latch is the slave latch. As a result of the change in the clock and date, the comparator generate a pulse and this pulse in turn sets the slave latch. The sense amplifier based comparator provide monotonic transitions from one to zero logic level on the outputs, following the leading clock edge. Any subsequent change of the data during the active clock interval will not affect the output of the sense amplifier based comparator. The S-R latch captures the transition and

holds the state until the next leading edge of the clock arrives. After the clock returns to inactive state, both of output of the sense amplifier based comparator rest to zero. Combing the comparator and the S-R latch, the whole part can be treated as the Flip Flop. Comparator is the pulse generator, and the S-R latch provide stable output of the comparator. The whole block is shown in the Fig.6.

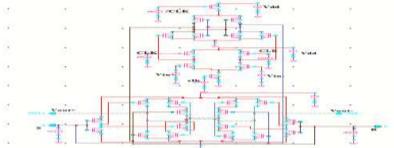


Fig.6: Comparator with the SR Latch (sense Amplifier Flip Flop)

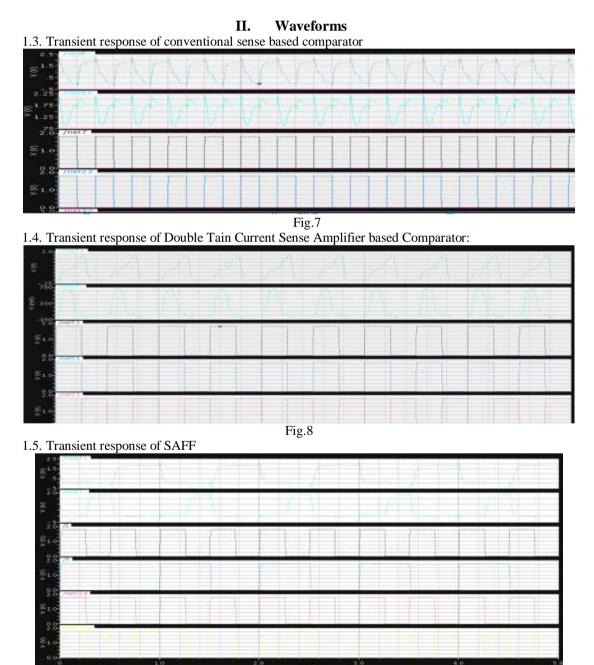
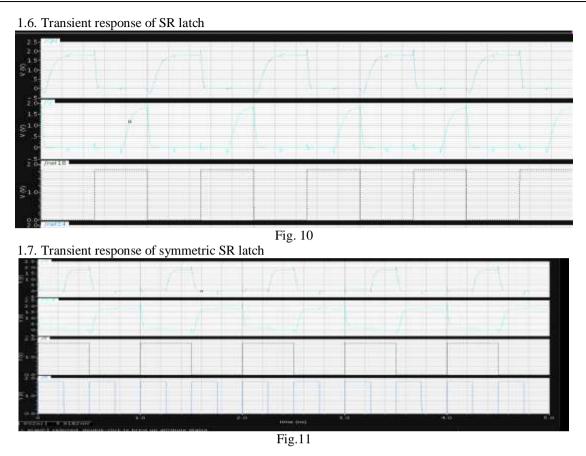


Fig.9 www.iosrjournals.org



III. Results Table 1.

| S.NO | DESIGN | DELAY in | DELAY |
|------|--|----------|---------|
| | | 180 nm | in 90nm |
| 1. | Conventional sense amplifier comparator | 0.22ns | 0.15ns |
| 2. | Double tail sense amplifier based comparator | 0.17ns | 0.106ns |
| 3. | Double tail sense amplifier based comparator with SR latch | 0.029ns | 0.011ns |
| | (SAFF) ,delay between the Q and Q_b | | |
| 4. | Conventional SR latch ,delay between the Q and Q_b | 0.082ns | 0.044ns |
| 5. | Symmetric SR latch , delay between the Q and Q_b | 0.035 ns | 0.019ns |

The average power dissipated in conventional sense amp is 63.6 pW(180nm),36.9pW(90nm) and in SAFF it is 42.1 pW. in 180 nm and 24.01 pW in 90nm

IV. Conclusion

1) The output of conventional sense based amp has been found to unstable and having delay.

2) The double tail current sense based comparator has fast response but unstable output.

3) The double tail current sense based comparator with symmetric SR latch(saff) has fast response and stable output.

4) The design has less delay and less power dissipation in 90 nm technology.

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